ZXMN2F34FH
20V SOT23 N-channel enhancement mode MOSFET

Summary

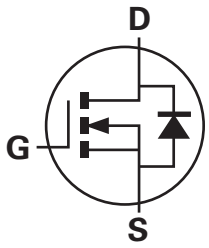
$V_{(BR)DSS}$	$R_{DS(on)}$ (Ω)	I_D (A)
20	0.060 @ V_{GS}= 4.5V	4.0
	0.120 @ V_{GS}= 2.5V	2.9

Description

This new generation Trench MOSFET from Zetex features low on-resistance achievable with low (2.5V) gate drive.

Features

- Low on-resistance
- 2.5V gate drive capability
- SOT23 package



Applications

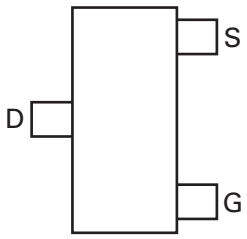
- Buck/Boost DC-DC Converters
- Motor Control
- LED Lighting

Ordering information

DEVICE	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMN2F34FHTA	7	8	3000

Device marking

KNB



Top view

Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Drain source voltage	V_{DSS}	20	V
Gate source voltage	V_{GS}	±12	V
Continous Drain Current @ V_{GS}=4.5; T_A=25°C[b] @ V_{GS}=4.5; T_A=70°C[b] @ V_{GS}=4.5; T_A=25°C[a]	I_D	4.0 3.3 3.4	A A A
Pulsed drain current[c]	I_{DM}	18.6	A
Continuous source current (body diode)[b]	I_S	2.1	A
Pulsed source current (body diode)[c]	I_{SM}	18.6	A
Power dissipation at T_A =25°C[a] Linear derating factor	P_D	0.95 7.6	W mW/°C
Power dissipation at T_A =25°C[b] Linear derating factor	P_D	1.4 11	W mW/°C
Operating and storage temperature range	T_j, T_{stg}	-55 to 150	°C

Thermal resistance

Parameter	Symbol	Limit	Unit
Junction to ambient[a]	$R_{\Theta JA}$	131	°C/W
Junction to ambient[b]	$R_{\Theta JA}$	89	°C/W
Junction to lead[d]	$R_{\Theta JL}$	68	°C/W

NOTES:

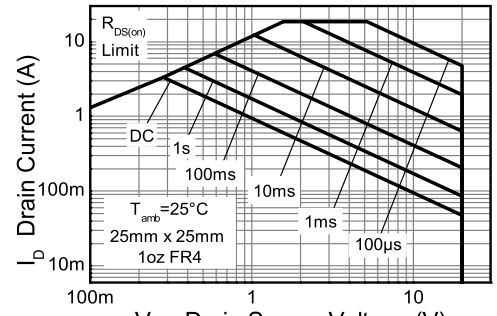
(a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

(b) For a device surface mounted on FR4 PCB measured at t≤ 5 sec.

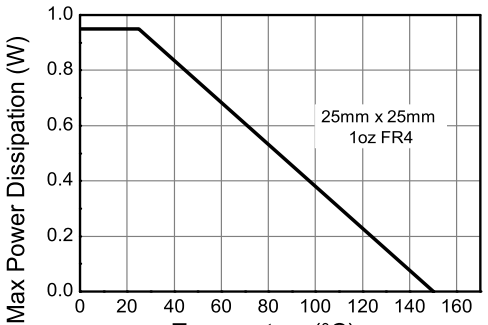
(c) Repetitive rating - 25mm x 25mm FR4 PCB, D=0.02, pulse width 300μs - pulse width limited by maximum junction temperature.

(d) Thermal resistance from junction to solder-point (at end of drain lead).

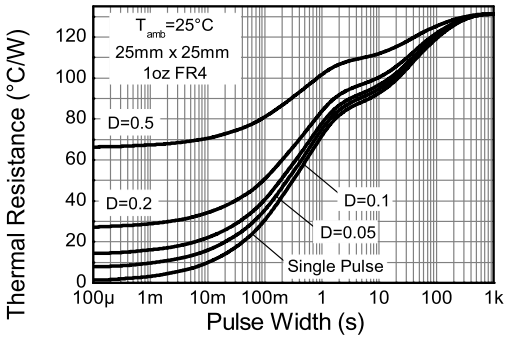
Thermal characteristics



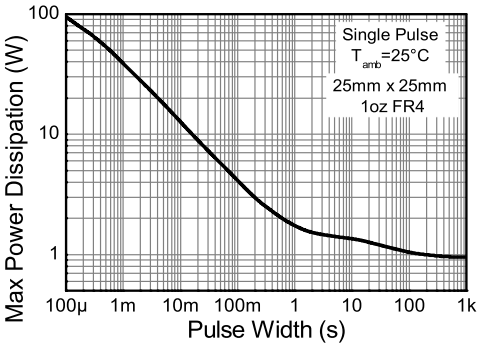
Safe Operating Area



Derating Curve



Transient Thermal Impedance



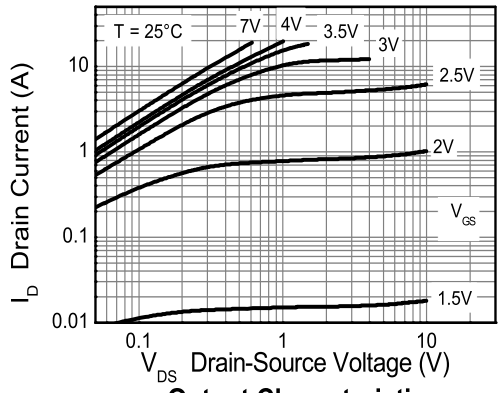
Pulse Power Dissipation

Electrical characteristics (at T_{amb} = 25°C unless otherwise stated)

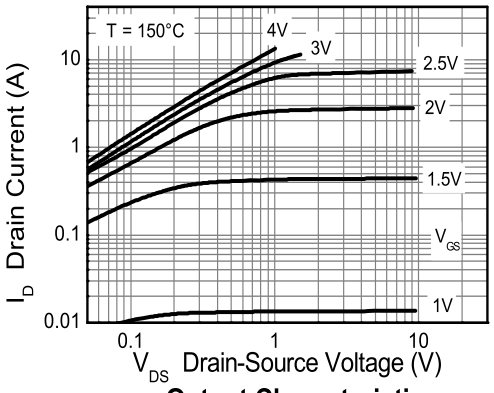
Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	20			V	I_D= 250μA, V_{GS}=0V
Zero Gate Voltage Drain Current	I_{DSS}			1	μA	V_{DS}= 20V, V_{GS}=0V
Gate-Body Leakage	I_{GSS}			100	nA	V_{GS}=±12V, V_{DS}=0V
Gate-Source Threshold Voltage	$V_{GS(th)}$	0.5	0.8	1.5	V	I_D= 250μA, V_{DS}=V_{GS}
Static Drain-Source On-State Resistance (*)	$R_{DS(on)}$			0.060 0.120	Ω Ω	V_{GS}= 4.5V, I_D= 2.5A V_{GS}= 2.5V, I_D= 1.0A
Forward Transconductance(*)(†)	g_{fs}		7.5		S	V_{DS}= 10V, I_D= 2.5A
Dynamic (†)						
Input Capacitance	C_{iss}		277		pF	V_{DS}= 10V, V_{GS}=0V f=1MHz
Output Capacitance	C_{oss}		65		pF	
Reverse Transfer Capacitance	C_{rss}		35		pF	
Switching (‡)(†)						
Turn-On-Delay Time	$t_{d(on)}$		2.65		ns	V_{DD}= 10V, V_{GS}= 4.5V I_D= 1A $R_G \approx 6.0\Omega$
Rise Time	t_r		4.2		ns	
Turn-Off Delay Time	$t_{d(off)}$		9.9		ns	
Fall Time	t_f		5.1		ns	
Total Gate Charge	Q_g		2.8		nC	V_{DS}= 10V, V_{GS}= 4.5V I_D= 2.5A
Gate-Source Charge	Q_{gs}		0.61		nC	
Gate Drain Charge	Q_{gd}		0.63		nC	
Source-drain diode						
Diode Forward Voltage(*)	V_{SD}		0.73	1.2	V	I_S= 1.25A, V_{GS}=0V
Reverse recovery time(†)	t_{rr}		6.5		ns	T_j=25°C, I_F=1.65A di/dt=100A/μs
Reverse recovery charge(†)	Q_{rr}		1.4		nC	

NOTES:
(*) Measured under pulsed conditions. Pulse width ≤ 300μs; duty cycle ≤2%.
(†) For design aid only, not subject to production testing.
(‡) Switching characteristics are independent of operating junction temperature.

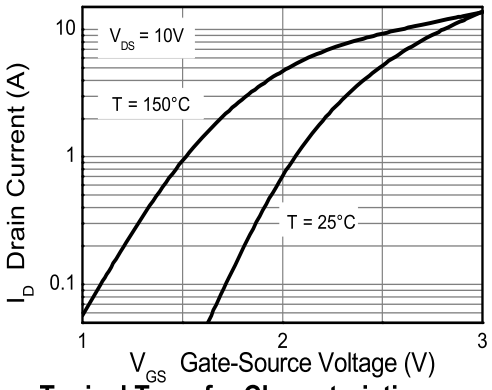
Typical characteristics



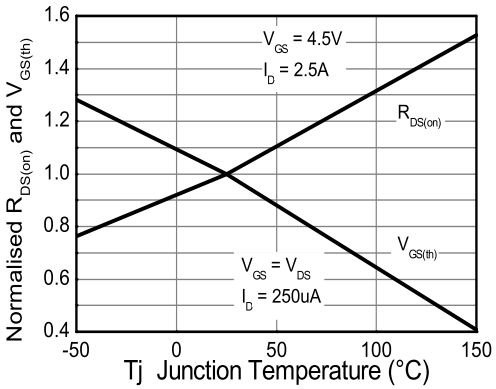
Output Characteristics



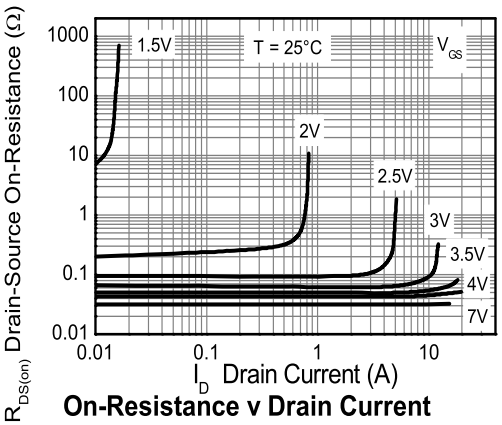
Output Characteristics



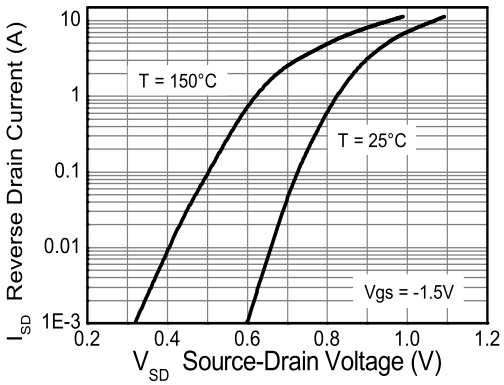
Typical Transfer Characteristics



Normalised Curves v Temperature

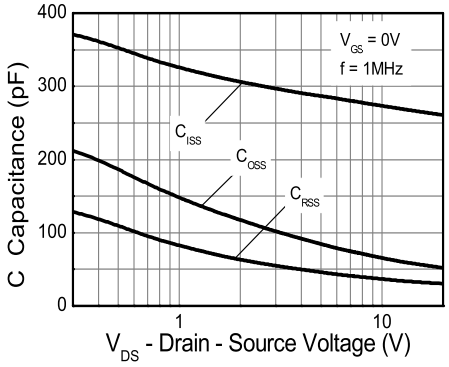


On-Resistance v Drain Current

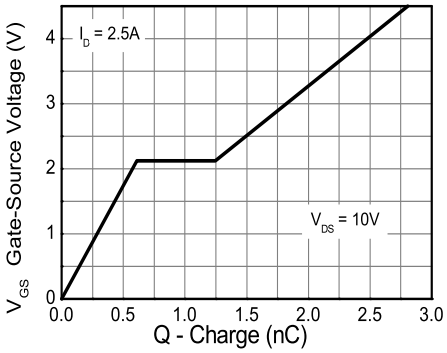


Source-Drain Diode Forward Voltage

Typical characteristics

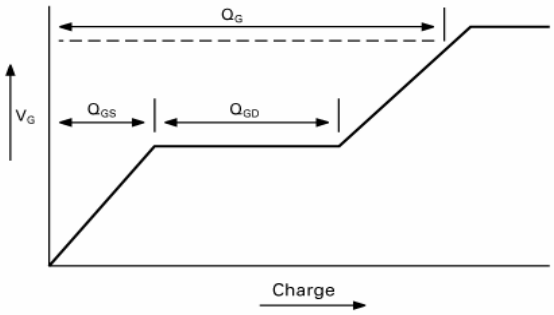


Capacitance v Drain-Source Voltage

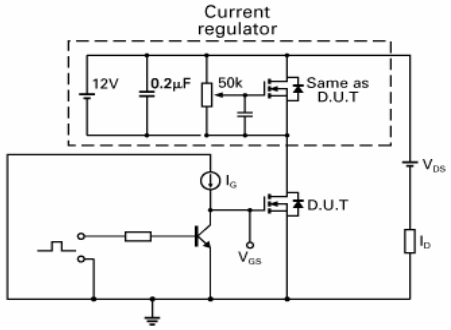


Gate-Source Voltage v Gate Charge

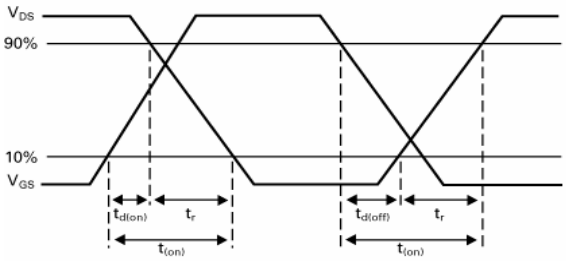
Test circuits



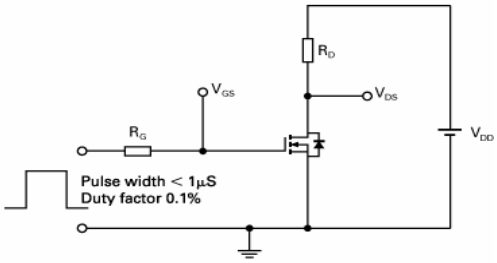
Basic gate charge waveform



Gate charge test circuit

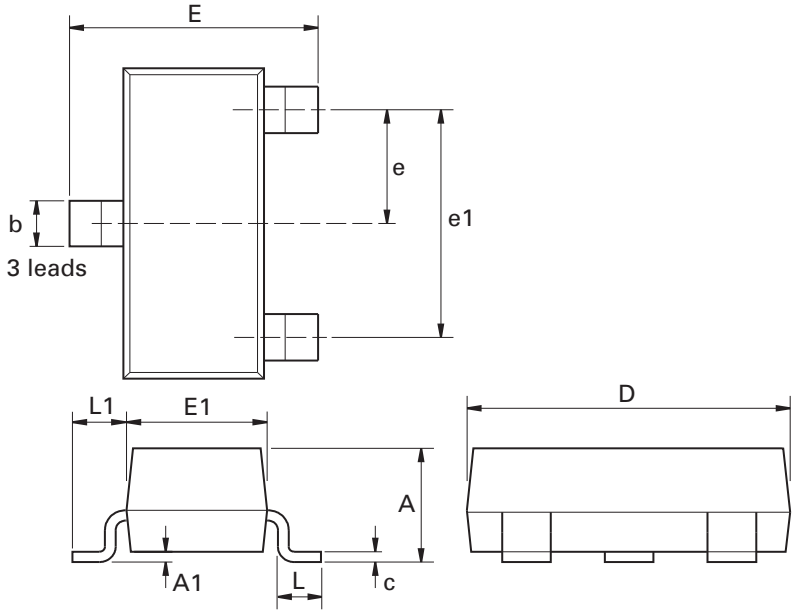


Switching time waveforms



Switching time test circuit

Package outline - SOT23



Dim.	Millimeters		Inches		Dim.	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	-	1.12	-	0.044	e1	1.90 NOM		0.075 NOM	
A1	0.01	0.10	0.0004	0.004	E	2.10	2.64	0.083	0.104
b	0.30	0.50	0.012	0.020	E1	1.20	1.40	0.047	0.055
c	0.085	0.20	0.003	0.008	L	0.25	0.60	0.0098	0.0236
D	2.80	3.04	0.110	0.120	L1	0.45	0.62	0.018	0.024
e	0.95 NOM		0.037 NOM		-	-	-	-	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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